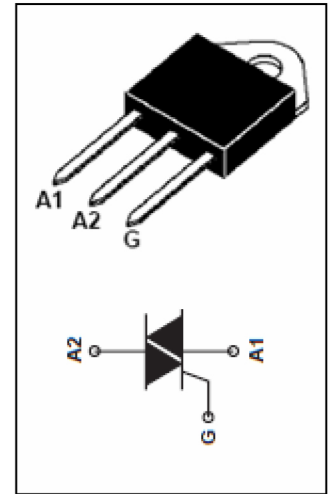


FEATURES

- With TO-3P insulated package
- Suitable for general purpose where high surge current capability is required. Application such as phase control and static switching on inductive or resistive load.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	MIN	UNIT
V _{DRM}	Repetitive peak off-state voltage	600	V
V _{RRM}	Repetitive peak reverse voltage	600	V
I _{T(RMS)}	RMS on-state current (full sine wave) T _j =90°C	25	A
I _{TSM}	Non-repetitive peak on-state current t _p =8.3ms	260	A
T _j	Operating junction temperature	125	°C
T _{stg}	Storage temperature	-45~150	°C
P _{G(AV)}	Average gate power dissipation(T _j =125°C)	1	W
R _{th(j-c)}	Thermal resistance, junction to case	1.5	°C/W
R _{th(j-a)}	Thermal resistance, junction to ambient	50	°C/W



ELECTRICAL CHARACTERISTICS (T_c=25°C unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT	
I _{RRM}	Repetitive peak reverse current	V _R =V _{RRM} , V _R =V _{RRM} , T _j =125°C	0.01 6.0	mA	
I _{DRM}	Repetitive peak off-state current	V _D =V _{DRM} , V _D =V _{DRM} , T _j =125°C	0.01 6.0	mA	
I _{GT}	Gate trigger current	V _D =12V; R _L = 33 Ω	I	50	mA
			II	50	
			III	50	
			IV	100	
I _H	Holding current	I _{GT} = 0.5A, Gate Open	80	mA	
V _{GT}	Gate trigger voltage all quadrant	V _D =12V; R _L = 33 Ω	1.5	V	
V _{TM}	On-state voltage	I _T = 35A; t _p = 380 μ s	1.7	V	